



Advance Program Part II

LATE NEWS PAPERS

Wednesday, September 13

Oral Session

Room 416/417(D)

17:45 D-2-7L Deep-Level Characterization of Tris(8-Hydroxyquinoline) Aluminum with and without Quinacridone Doping
Y. Nakano, K. Noda, H. Fujikawa, T. Morikawa and T. Ohwaki, *Toyota Central R&D Labs. Inc., Japan*

Room 511/512(I)

18:00 I-2-8L ZnO-based semiconductors for visible light emission devices
T. Ohashi, K. Yamamoto, A. Nakamura, T. Aoki and J. Temmyo, *Shizuoka Univ., Japan*

Thursday, September 14

Oral Session

Room 414/415 (C)

17:55 C-6-4L Scalable Wordline Shielding Scheme using Dummy Cell beyond 40nm NAND Flash Memory for Eliminating Abnormal Disturb of Edge Memory Cell
K. T. Park, S. C. Lee, J. Sel, J. Choi and K. Kim, *Samsung Electronics Corp., Korea*

Room 419 (F)

10:20 F-3-5L Detailed Balance in Quasi-Ballistic Electron Transport under Nanoscale Device Structures
H. Kusaka and N. Sano, *Univ. of Tsukuba, Japan*

P-11: Micro / Nano Electromechanical and Bio-Systems (Devices)

P-11-10L Characteristics of RF MEMS Switches for Communication Systems
Y. L. Lai and Y. H. Chen, *National Changhua Univ. of Education, Taiwan*

P-11-11L Investigation of Structures of Microwave MEMS Switches
Y. L. Lai and C. H. Lin, *National Changhua Univ. of Education, Taiwan*

Friday, September 15

Oral Session

Room 411/412 (A)

14:45 A-9-6L Room Temperature Demonstration of Variable Full Width at Half Maximum of Coulomb Oscillation in Silicon Single-Hole Transistor
K. Miyaji and T. Hiramoto, *Univ. of Tokyo, Japan*

Room 413 (B)

11:15 B-8-3L Tunable Slow Light of 1.3 μ m Region in Quantum Dots at Room Temperature
H. Gotoh^{1,2}, S. W. Chang¹, S. L. Chuang¹, H. Okamoto³ and Y. Shibata³, ¹Univ. of Illinois, ²NTT Basic Res. Labs. and ³NTT Photonics Labs., Japan

11:30 B-8-4L Integrated Optical Beam Splitters Employing Symmetric Mode Mixing in SiO₂/SiON/SiO₂ Multimode Interference (MMI) Waveguides
Z. L. Liao, R. Chuang and C. K. Chang, *National Cheng Kung Univ., Taiwan*

Room 416/417 (D)

16:15 D-10-5L Logic circuits with pentacene and ZnO transistors
H. Iechi^{1,2}, Y. Watanabe² and K. Kudo^{2,3}, ¹Ricoh Co. Ltd., ²Advanced Organic Device Project and ³Chiba Univ., Japan

Room 419 (F)

10:20 F-7-5L Tunnel Oxide Optimization to Improve Post-Cycling Retention of Flash Memories
W. H. Kwon, J. G. Jee, J. H. Han, J. I. Han, H. K. Lee, B. Y. Lee, S. P. Sim, C. K. Park and K. Kim, *Samsung Electronics Corp., Korea*

Room 501 (G)

9:00 G-7-1L The structural origin of determining the coefficient of thermal expansion for porous silica low-k films
M. Yamaji¹, N. Hata^{1,2}, T. Nakayama³, Y. Shishida³, Y. Hyodo³ and T. Kikkawa^{2,4}, ¹AIST, ²MIRAI-ASRC, ³MIRAI-ASET and ⁴Hiroshima Univ., Japan

17:45 F-6-4L Comparison of Threshold Voltage Fluctuations in Sub-45 nm Planar MOSFET and Thin-Buried-Oxide SOI Devices
Y. Li and S. M. Yu, *National Chiao Tung Univ., Taiwan*

Room 511/512 (I)

17:55 I-6-4L A 900-MHz Low-Noise Amplifier with High Tolerance for Noise Degradation due to a Leakage Signal from a Transmitter
R. Fujimoto, G. Takemura, M. Ishii, T. Toyoda and H. Tsurumi, *Toshiba Corp., Japan*

Poster Session (13:00–15:00)

Room 501 (G), 502 (H), 511/512 (I)

P-1: Advanced Gate Stack / Si Processing Science

P-1-29L Effect of Implanted Oxygen and Nitrogen on Mobility and Generation of Dislocation in SiGe/Si Heterostructure
A. Hara^{1,2}, N. Tamura¹ and T. Nakamura¹, ¹Fujitsu Labs. and ²Tohoku-Gakuin Univ., Japan

P-1-30L Guiding Principle of Energy Level Controllability of Silicon Dangling Bond in HfSiON
N. Umezawa¹, K. Shiraishi², S. Miyazaki³, A. Uedono², Y. Akasaka^{4,5}, S. Inumiya⁴, R. Hasunuma², K. Ymabe², H. Momida¹, T. Ohno¹, K. Ohmori¹, T. Chikyow¹, Y. Nara⁴ and K. Yamada⁶, ¹NIMS, ²Univ. of Tsukuba, ³Hiroshima Univ., ⁴Selete, ⁵TEL and ⁶Waseda Univ., Japan

P-3: CMOS Devices / Device Physics

P-3-27L Prominent Study on Si Substrate EM Loss and Suppressing Techniques
C. Y. Lee¹, J. D. S. Deng², J. X. Ye¹, C. Y. Wang¹ and C. H. Kao¹, ¹National Defense Univ. and ²Chung-Shang Inst. of Science and Technology, Taiwan

P-4: Advanced Memory Technology

P-4-13L Magnetically Damage-free Etching of MTJ Film for Future 0.24 μ m-rule-MRAMs
T. Mukai^{1,2}, N. Ohshima¹, H. Hada¹ and S. Samukawa², ¹NEC Corp. and ²Tohoku Univ., Japan

P-4-14L High Speed Resistive Switching in Pt/TiO₂/TiN Resistor for Multiple-Valued Memory Device
C. Yoshida, H. Noshiro, T. Iizuka, Y. Yamazaki, K. Kinoshita, M. Aoki and Y. Sugiyama, *Fujitsu Labs., Ltd., Japan*

Room 511/512 (I)

10:15 I-7-6L The Observation of Anomalous Optical Berthelot-type Behaviors in Quaternary AlInGaN Semiconductor Heterosystems
C. W. Hung¹, C. C. Ke¹, T. E. Nee¹, C. C. Chuo² and Z. H. Lee², ¹Chang Gung Univ. and ²Industrial Technology Research Inst., Taiwan

11:45 I-8-5L Low temperature (300°C) growth of crystalline/non-crystalline thin Si films by a newly developed single shower dual injection system employing microwave excited high density hydrogen plasma and silicon radicals CVD process.
T. Takeda¹, K. Tanaka¹, M. Saito¹, Y. Kato¹, T. Tsumori¹, H. Aharoni^{1,2} and T. Ohmi¹, ¹Tohoku Univ., ²Ben-Gurion Univ. of the Negev, Japan

UPDATED INFORMATION AND CORRECTION

P.31 Room 413

16:15 B-5-3

Systematic Study of the Effects of δ -p-doping on 1.3 μ m Quantum Dot Lasers
R. Alexander, H. Agarwal, K. M. Groom, H. Liu, M. Hopkinson and R. A. Hogg, *Univ. of Sheffield, UK*

Paper Title

P-9-8 Development of a Thermal Conductivity Prediction Simulator Including Conduction Electron and Lattice Vibration for Semiconductor, Insulator and Conduction Electron for Metal

P-11-5 Modifications on pH sensitivity of Si₃N₄ membrane by CF₄ plasma and rapid thermal annealing for ISFET/REFET applications

D-10-3 Self-Aligned Fabrication Process of Organic Thin-Film-Transistors on the Flexible Substrate Using Photo-Sensitive Self-Assembled Monolayers

Session Title

F-5 Device Fluctuation Analysis

F-6 Device Reliability and Characterization

I-8 Silicon-based Material Systems

P-4-15L Very low voltage operation of p-Si/Al₂O₃/HfO₂/TiO₂/Al₂O₃/Pt single quantum well flash memory devices with good retention
S. Maikap¹, P. J. Tzeng², T. Y. Wang³, S. S. Tseng⁴, C. H. Lin², H. Y. Lee², L. S. Lee², P. W. Li⁴, J. R. Yang³ and M. J. Tsai², ¹Chang Gung Univ., ²Industrial Technology Research Inst., ³Natinal Taiwan Univ. and ⁴National Central Univ., Taiwan

P-5: Advanced Circuits and Systems

P-5-11L A Novel Open-Loop High-Speed CMOS Sample-and-Hold
K. Hadidi, M. Mousazadeh and A. Khoei, *Urmia Univ., Iran*

P-5-12L Constant Magnetic Field Scaling in Inductive-Coupling Data Link
D. Mizoguchi, N. Miura, H. Ishikuro and T. Kuroda, *Keio Univ., Japan*

P-5-13L Scalable Motion Estimation Core for Multimedia System-on-Chip Applications
Y. K. Lai and T. E. Hsieh, *National Chung Hsing Univ., Taiwan*

P-5-14L Investigation of Analog Performance for Uniaxial Strained PMOSFETs
J. Kuo, W. Chen and P. Su, *National Chiao Tung Univ., Taiwan*

P-6: Compound Semiconductor Circuits, Electron Devices and Device Physics

P-6-10L High Power Performance of Metamorphic HEMTs using Pd Schottky contacts
Y. J. Li¹, J. S. Wu¹, H. C. Chiu² and Y. J. Chan¹, ¹National Central Univ. and ²Chang Gung Univ., Taiwan

P-6-11L Gate-Length Dependence of DC Characteristics in Submicron-Gate AlGaIn/GaN HEMTs
T. Ide¹, M. Shimizu¹, S. Yagi¹, M. Inada¹, G. Piao¹, Y. Yano², N. Akutsu², H. Okumura² and K. Arai², ¹AIST and ²Taiyo Nippon Sanso Corp., Japan

Session Chairs

B-7 L. Young (Hitachi) → Y. Lee (Hitachi)

C-3 H. Yamauchi (Sanyo Electric) → H. Yamauchi (Samsung Electronics)

E-5 H. Hwang (Gwangju Inst. of Sci. & Tech.) → T. Aoyama (Selete)

H-1 D. Hisasmoto (Hitachi) → D. Hisamoto (Hitachi)

I-1 H. Yamaguchi (NTT) → K. Yamaguchi (Univ. of Electro-Communications)

I-7 S. Shimomura (Osaka Univ.) → S. Shimomura (Ehime Univ.)

P10 (Short Presentation)
K. Kubo (Chiba Univ.) → T. Minakata (Asahi-KASEI)

Authors Name

F-1-2 N. Schaver → N. Schauer

Rump Sessions

Session A Panelists: T. Shimoda → T. Higuchi (Seiko Epson, Japan)

Cancel

D-6-4 Room 416/417(D) 17:25, Sept. 14

B-9-3 Room 413(B) 13:45, Sept. 15

Session Time

D-7 9:45-10:30

Session ID No. / Session Time

14:00 B-9-4 → 13:45 B-9-3

14:15 B-9-5 → 14:00 B-9-4

14:30 B-9-6 → 14:15 B-9-5

14:45 B-9-7 → 14:30 B-9-6

SSDM 2006 Time Table

Wednesday, September 13										
MAIN HALL										
10:00-12:20 PL: Opening Session/SSDM & Paper Award										
Room 411/412 (A)	Room 413 (B)	Room 414/415 (C)	Room 416/417 (D)	Room 418 (E)	Room 419 (F)	Room 501 (G)	Room 502 (H)	Room 511/512 (I)	Small Auditorium (J)	
14:00-15:45 Area 9: Physics and Applications of Novel Functional Materials and Devices A-1: Novel Devices and Characterization	14:00-16:00 Area 7: Photonic Devices and Device Physics B-1: Special Session : Photonic Crystals and Si Photonics I	14:00-16:20 Area 5: Advanced Circuits and Systems C-1: MEMS and Modeling	14:00-15:30 Area 10: Organic Materials Science, Device Physics, and Applications D-1: Organic Light Emitting Diodes	14:00-15:45 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics E-1: High-Speed Devices and ICs	14:00-15:50 Area 4: Advanced Memory Technology F-1: FeRAM	14:00-15:50 Area 2: Characterization and Materials Engineering for Interconnect Integration G-1: Advanced Metallization	14:00-16:00 Area 3: CMOS Devices /Device Physics H-1: CMOS Performance Enhancement Technology I	14:00-15:45 Area 8: Advanced Material Synthesis and Crystal Growth Technology I-1: Nanotechnology Fabrication	14:00-16:00 Area 1: Advanced Gate Stack /SI Processing Science J-1: Metal/High-k Gate Stack	
16:15-18:00 Area 9: Physics and Applications of Novel Functional Materials and Devices A-2: Novel Optical Devices	16:15-18:00 Area 7: Photonic Devices and Device Physics B-2: Special Session : Photonic Crystals and Si Photonics II	16:30-18:10 Area 5: Advanced Circuits and Systems C-2: Wireless Interconnect	16:00-18:00 Area 10: Organic Materials Science, Device Physics, and Applications D-2: Organic Light Emitting Diodes and Solar Cells	16:15-17:45 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics E-2: Wide-Bandgap Devices	16:15-18:00 Area 4: Advanced Memory Technology F-2: DRAM	16:15-18:00 Area 2: Characterization and Materials Engineering for Interconnect Integration G-2: Characterization I	16:15-18:00 Area 3: CMOS Devices /Device Physics H-2: CMOS Performance Enhancement Technology II	16:15-18:15 Area 8: Advanced Material Synthesis and Crystal Growth Technology I-2: Compound Semiconductors	16:15-18:00 Area 1: Advanced Gate Stack /SI Processing Science J-2: FUSI Gate Electrode	
18:30-20:30 Banquet/Young Award (Intercontinental Hotel, Pacific 3F)										
Thursday, September 14										
Room 411/412 (A)	Room 413 (B)	Room 414/415 (C)	Room 416/417 (D)	Room 418 (E)	Room 419 (F)	Room 501 (G)	Room 502 (H)	Room 511/512 (I)	Small Auditorium (J)	
9:00-10:30 Area 11: Micro/nano Electromechanical and Bio-Systems (Devices) A-3: MEMS and NEMS : Fabrication	9:00-10:30 Area 7: Photonic Devices and Device Physics B-3: LEDs and Lasers	9:00-10:20 Area 5: Advanced Circuits and Systems C-3: Toward Next Generation Systems	9:00-10:30 Area 10: Organic Materials Science, Device Physics, and Applications D-3: Organic Materials and Device Physics I	9:00-10:00 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics E-3: Sensors and Interface Physics	9:00-10:35 Area 3: CMOS Devices /Device Physics F-3: Quasi-Ballistic Transport	(Poster setting)	(Poster setting)	(Poster setting)	9:10-10:40 Area 1: Advanced Gate Stack /SI Processing Science J-3: Characterization of Gate Stack	
10:45-12:15 Short Presentation Area 11 and Area 8	10:45-12:15 Short Presentation Area 7 and Area 4	10:45-12:15 Short Presentation Area 5 and Area 2	10:45-11:30 Area 10: Organic Materials Science, Device Physics, and Applications D-4: Organic Materials and Device Physics II	10:45-12:15 Short Presentation Area 6 and Area 9	10:45-12:15 Short Presentation Area 3	(Poster setting)	(Poster setting)	(Poster setting)	10:45-12:15 Short Presentation Area 1	
11:30-12:30 Short Presentation Area 10										
13:00-15:00 Poster Session										
15:15-16:15 Joint Area 8 and 9 A-5: Nanowires and Nanotubes I	15:15-16:30 Area 7: Photonic Devices and Device Physics B-5: Quantum-dot Lasers	15:15-16:25 Area 4: Advanced Memory Technology C-5: ReRAM	15:15-16:15 Area 2: Characterization and Materials Engineering for Interconnect Integration D-5: Emerging Interconnect	15:15-16:35 Area 1: Advanced Gate Stack/SI Processing Science E-5: Junction I	15:15-16:35 Area 3: CMOS Devices /Device Physics F-5: Device Fluctuation Analysis	(Poster removed by 15:30 and Preparation for Rump Session)	(Poster removed by 15:30 and Preparation for Rump Session)	(Poster removed)	15:15-16:35 Area 1: Advanced Gate Stack /SI Processing Science J-5: High-k Dielectrics I	
16:30-18:00 Joint Area 8 and 9 A-6: Nanowires and Nanotubes II	16:45-18:00 Area 7: Photonic Devices and Device Physics B-6: Quantum Optical Devices	16:45-18:15 Area 4: Advanced Memory Technology C-6: Flash Memory I	16:25-17:25 Area 2: Characterization and Materials Engineering for Interconnect Integration D-6: Assembly and Packaging	16:45-17:25 Area 1: Advanced Gate Stack/SI Processing Science E-6: Junction II	16:45-18:00 Area 3: CMOS Devices /Device Physics F-6: Device Reliability and Characterization			16:45-18:05 Area 5: Advanced Memory Technology I-6: Analog Circuit Techniques	16:45-17:45 Area 1: Advanced Gate Stack /SI Processing Science J-6: Interface Properties of Ge	
18:30-20:30 Rump Session Room 501 "Challenges of New Non-Volatile Memories : Innovative Strategies to catch up with FLASH" Room 502 "Nanotechnology - Impact on Electronics, Photonics and Biology-"										
Friday, September 15										
Room 411/412 (A)	Room 413 (B)	Room 414/415 (C)	Room 416/417 (D)	Room 418 (E)	Room 419 (F)	Room 501 (G)	Room 502 (H)	Room 511/512 (I)	Small Auditorium (J)	
9:00-10:30 Area 9: Physics and Applications of Novel Functional Materials and Devices A-7: Novel Devices and Materials I	9:00-10:30 Area 7: Photonic Devices and Device Physics B-7: Micro-Optics and Optical Waveguides	9:00-10:30 Area 11: Micro/nano Electromechanical and Bio-Systems (Devices) C-7: Micro and Nano Fluidics for Biosensing	9:45-10:30 Area 10: Organic Materials Science, Device Physics, and Applications D-7: Molecular Electronics		9:00-10:20 Area 4: Advanced Memory Technology F-7: Flash Memory II	9:00-10:40 Area 2: Characterization and Materials Engineering for Interconnect Integration G-7: Characterization II	9:00-10:40 Area 3: CMOS Devices /Device Physics H-7: Compact Modeling	9:00-10:15 Area 8: Advanced Material Synthesis and Crystal Growth Technology I-7: Novel Materials	9:00-10:40 Area 1: Advanced Gate Stack /SI Processing Science J-7: High-k Dielectrics II	
10:45-12:15 Area 9: Physics and Applications of Novel Functional Materials and Devices A-8: Novel Devices and Materials II	10:45-12:00 Area 7: Photonic Devices and Device Physics B-8: All-Optical Switches	10:45-12:15 Area 11: Micro/nano Electromechanical and Bio-Systems (Devices) C-8: Nano and Bio Sensors I	10:45-12:00 Area 10: Organic Materials Science, Device Physics, and Applications D-8: Organic Transistor I	10:45-12:15 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics E-8: GaAs FETs and Process Technologies	10:45-12:25 Area 4: Advanced Memory Technology F-8: MRAM/PRAM	10:45-12:25 Area 2: Characterization and Materials Engineering for Interconnect Integration G-8: Special Session I ; Reliability	10:45-12:25 Area 3: CMOS Devices /Device Physics H-8: Advanced Channel and Substrate Technology	10:45-11:45 Area 8: Advanced Material Synthesis and Crystal Growth Technology I-8: Silicon-based Material Systems	10:45-12:25 Area 1: Advanced Gate Stack /SI Processing Science J-8: Metal/High-k CMOS	
13:15-14:45 Area 9: Physics and Applications of Novel Functional Materials and Devices A-9: Novel Devices and Materials III	13:15-14:45 Area 7: Photonic Devices and Device Physics B-9: Detectors and Sensors	13:15-15:00 Area 11: Micro/nano Electromechanical and Bio-Systems (Devices) C-9: Nano and Bio Sensors II	13:30-15:00 Area 10: Organic Materials Science, Device Physics, and Applications D-9: Organic Transistor II	13:15-15:00 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics E-9: GaN FETs and Process Technologies	13:15-14:55 Area 3: CMOS Devices /Device Physics F-9: Schottky S/D and Carrier Transport	13:15-15:35 Area 2: Characterization and Materials Engineering for Interconnect Integration G-9: Special SessionII ; Metallization Challenges	13:15-14:55 Area 3: CMOS Devices /Device Physics H-9: Carrier Transport		13:15-15:05 Area 1: Advanced Gate Stack /SI Processing Science J-9: Reliability	
		15:15-16:30 Area 11: Micro/nano Electromechanical and Bio-Systems (Devices) C-10: MEMS and NEMS : Application	15:15-16:15 Area 10: Organic Materials Science, Device Physics, and Applications D-10: Organic Transistor III	15:15-17:00 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics E-10: High-Voltage GaN Devices			15:15-16:55 Area 3: CMOS Devices /Device Physics H-10: Advanced Device Technology		15:15-16:35 Area 1: Advanced Gate Stack /SI Processing Science J-10: Metal Gate Electrode	

SSDM 2006 Chairpersons List

Day	Main Hall										
	Room 411/412 (A)	Room 413 (B)	Room 414/415 (C)	Room 416/417 (D)	Room 418 (E)	Room 419 (F)	Room 501 (G)	Room 502 (H)	Room 511/512 (I)	Small Auditorium (J)	
Wednesday, September 13	Main Hall (10:00-12:20) T. Hiramoto (Univ. of Tokyo) Y. Hirayama (Tohoku Univ.)										
	A-1 (14:00-15:45) J. Motohisa (Hokkaido Univ.) Y. Nakamura (NEC)	B-1 (14:00-15:45) S. Noda (Kyoto Univ.) M. Tokushima (NEC)	C-1-1 (14:00-15:20) T. Komuro (Agilent Technologies International Japan) K. Masu (Tokyo Tech) C-1-2 (15:20-16:20) T. Hamasaki (Texas Instruments Japan) M. Horiguchi (Renesas)	D-1 (14:00-15:30) Y. Ohmori (Osaka Univ.) T. Sano (Sanyo Electric)	E-1 (14:00-15:45) K. Maezawa (Nagoya Univ.) S. Yamahata (NTT)	F-1 (14:00-15:50) T. Eshita (Fujitsu) H.S. Jeong (Samsung Electronics)	G-1 (14:00-15:50) S. Ogawa (Selete/Matsushita) K. Ueno (Shibaura Inst. of Tech.)	H-1 (14:00-16:00) K. Shibahara (Hiroshima Univ.) D. Hisasmoto (Hitachi)	I-1 (14:00-15:45) T. Sogawa (NTT) K. Yamaguchi (Univ. of Electro-Communications)	J-1 (14:00-16:00) Y. Nara (Selete) J. Yugami (Renesas)	
Thursday, September 14	A-2 (16:15-18:00) T. Usuki (Fujitsu Labs.) Y. Ohno (Tohoku Univ.)	B-2 (16:15-17:45) O. Wada (Kobe Univ.) H. Yamada (NEC)	C-2-1 (16:30-17:30) M. Horiguchi (Renesas) R. Fujimoto (Toshiba) C-2-2 (17:30-18:10) R. Fujimoto (Toshiba) T. Hamasaki (Texas Instruments Japan)	D-2-1 (16:00-16:30) T. Someya (Univ. of Tokyo)	E-2 (16:15-17:45) Y. Ohno (Univ. of Tokushima) S. Kuroda (Eudina Devices)	F-2 (16:15-18:05) I. Asano (Elpida) H.S. Jeong (Samsung Electronics)	G-2 (16:15-18:05) N. Hata (AIST) F. Mizuno (Meisei Univ.)	H-2 (16:15-17:55) F. Boeuf (STMicroelectronics) H. Oda (Renesas)	I-2 (16:15-18:15) K. H. Ploog (Paul Drude Inst.) D. Iwai (Fujitsu Labs.)	J-2 (16:15-17:55) K. Shiraishi (Univ. of Tsukuba) E. Cartier (IBM)	
	A-3 (9:00-10:30) T. Nishimoto (Shimadzu) T. Ono (Tohoku Univ.)	B-3 (9:00-10:30) M. Ezaki (Toshiba) M. Sugawara (Fujitsu Labs.)	C-3-1 (9:00-9:40) H. Yamauchi (Samsung Electronics) H. Kobayashi (Gunma Univ.) C-3-2 (9:40-10:20) K. Masu (Tokyo Tech) H. Yamauchi (Samsung Electronics)	D-3 (9:00-10:30) K. Kato (Niigata Univ.) T. Sano (Sanyo Electric)	E-3 (9:00-10:00) T. Hashizume (Hokkaido Univ.) K. Kumakura (NTT)	F-3 (9:00-10:35) Y. Kamakura (Osaka Univ.) K. Kurimoto (Matsushita Electric)				J-3 (9:10-10:40) S. Miyazaki (Hiroshima Univ.) A. Sakai (Nagoya Univ.)	
	A-4 Short Presentation H. Tabata (Osaka Univ.)	B-4 Short Presentation M. Sugawara (Fujitsu Labs.)	C-4 Short Presentation H. Kobayashi (Gunma Univ.)	D-4-1 (10:45-11:30) M. Iwamoto (Tokyo Tech) K. Kato (Niigata Univ.) D-4-2 Short Presentation T. Minakata (Asahi Kasei)	E-4 Short Presentation M. Kuzuhara (Univ. of Fukui)	F-4 Short Presentation H. Oda (Renesas)				J-4 Short Presentation Y. Nara (Selete)	
	A-5 (15:15-16:15) T. Fukui (Hokkaido Univ.) Y. L. Foo (Inst. of Materials Research and Engineering)	B-5 (15:15-16:30) M. Sugawara (Fujitsu Labs.) K. Komori (AIST)	C-5 (15:15-16:25) Y. Ohji (Renesas) I. Asano (Elpida)	D-5 (15:15-16:15) T. Yoda (Toshiba) T. Tatsumi (Sony)	E-5 (15:15-16:35) B. Mizuno (UJT Lab.) T. Aoyama (Selete)	F-5 (15:15-16:25) Y. Kamakura (Osaka Univ.) J. C. S. Woo (UCLA)				J-5 (15:15-16:35) Y. Tsunashima (Toshiba) T. Nabatame (ASET)	
Friday, September 15	A-6 (16:30-18:00) K. Matsumoto (Osaka Univ.) Y. Awano (Fujitsu Labs.)	B-6 (16:45-18:00) L. Lester (Univ. of New Mexico) T. Usuki (Univ. of Tokyo)	C-6 (16:45-18:15) Y. Yamauchi (Sharp) Y. Shimamoto (Hitachi)	D-6 (16:25-17:25) S. H. Brongersma (IMEC) D. Y. Yoon (Seoul National Univ.)	E-6 (16:45-17:45) B. Mizuno (UJT Lab.) H. Fukutome (Fujitsu Labs.)	F-6 (16:45-18:00) D. Hisasmoto (Hitachi) Y. Momiyama (Fujitsu)			I-6 (16:45-18:15) H. Kobayashi (Gunma Univ.) T. Komuro (Agilent Technologies International Japan)	J-6 (16:45-17:45) K. Shiraishi (Univ. of Tsukuba) A. Sakai (Nagoya Univ.)	
	A-7 (9:00-10:30) H. Mizuta (Tokyo Tech) Y. Suda (Tokyo Univ. of Agri. & Tech.)	B-7 (9:00-10:30) Y. Lee (Hitachi) S. Nishikawa (Mitsubishi Electric)	C-7 (9:00-10:30) Y. Takamura (JAIST) H. Oana (Univ. of Tokyo)	D-7 (9:45-10:30) T. Someya (Univ. of Tokyo) K. Kato (Niigata Univ.)		F-7 (9:00-10:40) C. Hsu (eMemory Tech.) Y. Yamauchi (Sharp)	G-7 (9:00-10:40) M. Kodera (Toshiba) M. Matsuura (Renesas)	H-7 (9:00-10:20) A. Asenov (Glasgow Univ.) K. Kurimoto (Matsushita Electric)	I-7 (9:00-10:15) S. Shimomura (Ehime Univ.) D. Iwai (Fujitsu Labs.)	J-7 (9:00-10:40) Y. Nara (Selete) A. Toriumi (Univ. of Tokyo)	
	A-8 (10:45-12:15) Y. Takahashi (Hokkaido Univ.) M. Tabe (Shizuoka Univ.)	B-8 (10:45-11:45) M. Sugawara (Fujitsu Labs.) M. Tokushima (NEC)	C-8 (10:45-12:15) K. Sawada (Toyohashi Univ. of Tech.) S. A. Contera (Univ. of Oxford)	D-8 (10:45-12:00) K. Kudo (Chiba Univ.) M. Iwamoto (Tokyo Tech)	E-8 (10:45-12:15) Y. J. Chan (National Chiao Tung Univ.) S. Tanaka (NEC)	F-8 (10:45-12:25) Y. Ohji (Renesas) N. Ishiwata (NEC)	G-8 (10:45-12:25) S. Ogawa (Selete/Matsushita) Y. Hayashi (NEC)	H-8 (10:45-12:05) Y. Momiyama (Fujitsu) K. Takeuchi (NEC)	I-8 (10:45-12:00) K. Nishi (NEC) H. Yamaguchi (NTT)	J-8 (10:45-12:25) Y. Tsunashima (Toshiba) O. Faynot (LETT)	
	A-9 (13:15-15:00) K. Ishibashi (RIKEN) T. Fujisawa (NTT)	B-9 (13:15-14:45) M. Tokushima (NEC) M. Sugawara (Fujitsu Labs.)	C-9 (13:15-15:00) H. Tabata (Osaka Univ.) H. Sugihara (Matsushita Electric)	D-9 (13:30-15:00) M. Iwamoto (Tokyo Tech) T. Someya (Univ. of Tokyo)	E-9 (13:15-15:00) R. Hattori (Mitsubishi Electric) M. Kuzuhara (Univ. of Fukui)	F-9 (13:15-14:35) A. Hokazono (Toshiba) J. C. S. Woo (UCLA)	G-9 (13:15-15:35) J. Koike (Tohoku Univ.) M. Nihei (Selete/Fujitsu)	H-9 (13:15-14:55) H. C. Lin (National Chiao Tung Univ.) K. Takeuchi (NEC)		J-9 (13:15-15:05) J. Yugami (Renesas) S. Miyazaki (Hiroshima Univ.)	
		C-10 (15:15-16:30) Y. Yoshino (Murata Mfg.) T. Ono (Tohoku Univ.)	D-10 (15:15-16:30) K. Kudo (Chiba Univ.) T. Someya (Univ. of Tokyo)	E-10 (15:15-17:00) A. Nakagawa (New Japan Radio) T. Tanaka (Matsushita Electric)			H-10 (15:15-16:55) K. Shibahara (Hiroshima Univ.) A. Hokazono (Toshiba)		J-10 (15:15-16:35) T. Nabatame (ASET) H. Fukutome (Fujitsu Labs.)		